

To all our customers

Regarding the change of names mentioned in the document, such as Mitsubishi Electric and Mitsubishi XX, to Renesas Technology Corp.

The semiconductor operations of Hitachi and Mitsubishi Electric were transferred to Renesas Technology Corporation on April 1st 2003. These operations include microcomputer, logic, analog and discrete devices, and memory chips other than DRAMs (flash memory, SRAMs etc.) Accordingly, although Mitsubishi Electric, Mitsubishi Electric Corporation, Mitsubishi Semiconductors, and other Mitsubishi brand names are mentioned in the document, these names have in fact all been changed to Renesas Technology Corp. Thank you for your understanding. Except for our corporate trademark, logo and corporate statement, no changes whatsoever have been made to the contents of the document, and these changes do not constitute any alteration to the contents of the document itself.

Note : Mitsubishi Electric will continue the business operations of high frequency & optical devices and power devices.

Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

FL14KM-12A

HIGH-SPEED SWITCHING USE

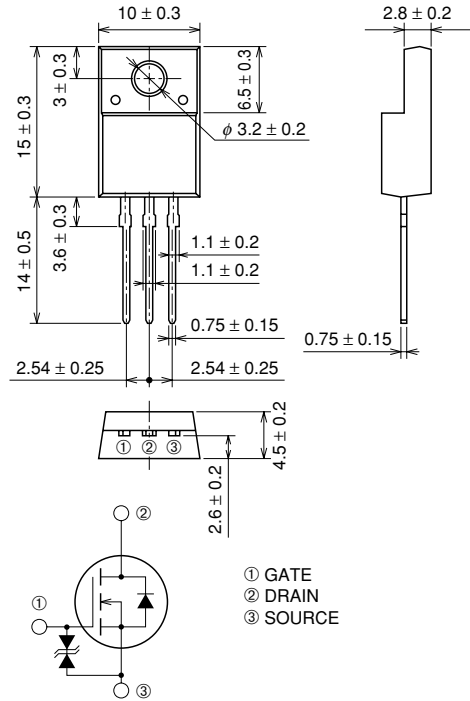
FL14KM-12A



- 10V DRIVE
- V_{DSS} 600V
- r_{DS (ON)} (MAX) 0.75Ω
- I_D 14A

OUTLINE DRAWING

Dimensions in mm



TO-220FN

APPLICATION

SMPS, Inverter type fluorescent light sets, etc.

MAXIMUM RATINGS (T_c = 25°C)

Symbol	Parameter	Conditions	Ratings	Unit
V _{DSS}	Drain-source voltage	V _{GS} = 0V	600	V
V _{GSS}	Gate-source voltage	V _{DS} = 0V	±30	V
I _D	Drain current		14	A
I _{DM}	Drain current (Pulsed)		42	A
I _{DA}	Avalanche current (Pulsed)	L = 200μH	14	A
P _D	Maximum power dissipation		40	W
T _{ch}	Channel temperature		-55 ~ +150	°C
T _{stg}	Storage temperature		-55 ~ +150	°C
V _{iso}	Isolation voltage	AC for 1minute, Terminal to case	2000	V
—	Weight	Typical value	2.0	g

FL14KM-12A

HIGH-SPEED SWITCHING USE

ELECTRICAL CHARACTERISTICS (T_{ch} = 25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
V (BR) DSS	Drain-source breakdown voltage	I _D = 1mA, V _{GS} = 0V	600	—	—	V
V (BR) GSS	Gate-source breakdown voltage	I _G = ±100μA, V _{DS} = 0V	±30	—	—	V
I _{GSS}	Gate-source leakage current	V _{GS} = ±25V, V _{DS} = 0V	—	—	±10	μA
I _{DSS}	Drain-source leakage current	V _{DS} = 600V, V _{GS} = 0V	—	—	1	mA
V _{GS} (th)	Gate-source threshold voltage	I _D = 1mA, V _{DS} = 10V	2.0	3.0	4.0	V
r _{DS} (ON)	Drain-source on-state resistance	I _D = 7A, V _{GS} = 10V	—	0.58	0.75	Ω
V _{DS} (ON)	Drain-source on-state voltage	I _D = 7A, V _{GS} = 10V	—	4.06	5.25	V
y _{fs}	Forward transfer admittance	I _D = 7A, V _{DS} = 10V	—	11	—	S
C _{iss}	Input capacitance	V _{DS} = 25V, V _{GS} = 0V, f = 1MHz	—	1600	—	pF
C _{oss}	Output capacitance		—	210	—	pF
C _{rss}	Reverse transfer capacitance		—	80	—	pF
t _d (on)	Turn-on delay time		—	30	—	ns
t _r	Rise time	V _{DD} = 200V, I _D = 7A, V _{GS} = 10V, R _{GEN} = R _{GS} = 50Ω	—	60	—	ns
t _d (off)	Turn-off delay time		—	290	—	ns
t _f	Fall time		—	120	—	ns
V _{SD}	Source-drain voltage		I _S = 7A, V _{GS} = 0V	—	1.5	2.0
R _{th} (ch-c)	Thermal resistance	Channel to case	—	—	3.13	°C/W